Diode Semiconductor Device - Page 1 of 1



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Inclosure M	Naterial:
Glass	
Overall Ler	ngth:
0.300 inche	s
Terminal L	ength:
1.500 inche	s
Overall Dia	meter:
0.107 inche	s
End Applic	cation:
Strategic we	eapon systems (poseidon and trident); support equipment, f-111 aircraf
Mounting M	Method:
Terminal	
Features P	rovided:
Hermetically	y sealed case
Criticality (Code Justification:
Feat	
Semicondu	uctor Material:
Silicon	
Voltage Ra	ting In Volts Per Characteristic:
40.0 workir	ng peak reverse voltage, peak total value
Current Ra	ting Per Characteristic:
200.00 micr	roamperes forward current, average peak
Power Rati	ng Per Characteristic:
500.0 milliw	atts small-signal input power, common-collector absolute
Maximum (Operating Tempurature Per Measurement Point:
175.0 degre	ees celsius junction
Special Fea	atures:
Weapon sy	stem essential
Terminal T	ype And Quantity:
2 uninsulate	ed wire lead
Shelf Life:	
N/a	
Unit Of Mea	asure:
Demilitariz	ation:
No	
Fiig:	
- 3-	